

## Refine Search

### Search Results -

Terms	Documents
L9	0

Database:

US Pre-Grant Publication Full-Text Database  
 US Patents Full-Text Database  
 US OCR Full-Text Database  
 EPO Abstracts Database  
 JPO Abstracts Database  
 Derwent World Patents Index  
**IBM Technical Disclosure Bulletins**

Search:

L10

Recall Text

Clear

Refine Search

Interrupt

### Search History

**DATE:** Thursday, January 27, 2005    [Printable Copy](#)    [Create Case](#)

**Set Name Query**

side by side

**Hit Count Set Name**

result set

*DB=TDBD; PLUR=YES; OP=OR*L10    L90    L10*DB=DWPI; PLUR=YES; OP=OR*L9    L80    L9*DB=JPAB; PLUR=YES; OP=OR*L8    L70    L8*DB=EPAB; PLUR=YES; OP=OR*L7    L60    L7*DB=USOC; PLUR=YES; OP=OR*L6    L50    L6*DB=PGPB; PLUR=YES; OP=OR*L5    L40    L5*DB=USPT; PLUR=YES; OP=OR*L4    L3 and leakage1    L4L3    L2 and "read transistor" and "storage transistor"1    L3

<u>L2</u>	L1 and ("5 nanometers" near7 channel)	5	<u>L2</u>
<u>L1</u>	memory	480633	<u>L1</u>

END OF SEARCH HISTORY